

Q1 --3. (amended) Method according to Claim 1 characterized in that the doping material (2) is first applied to the substrate, after which the barrier material (5, 5', 5") is applied to the substrate on the doping material (2).--

--4. (amended) Method according to claim 1, characterized in that the diffusion barrier material (5, 5', 5") is a dielectric material in paste form that is sintered after being applied to the substrate (1).--

Q2 --6. (amended) Method according to claim 1, characterized in that the surface resistance of the highly doped regions is between 10 and 60 ohm square and the surface resistance of the regions of low doping is between 30 and 500 ohm square.--

Q3 --8. (amended) Method according to claim 1, characterized in that an etching material is added to the diffusion material (5, 5', 5") to etch away the substrate.--

Please add the following claim:

Q4 --9. (new) Method according to Claim 2 characterized in that the doping material (2) is first applied to the substrate, after which the barrier material (5, 5', 5") is applied to the substrate on the doping material (2).----

REMARKS

Claim 9 has been added.

Claims 3, 4, 6, and 8 have been amended to eliminate multiple dependencies.